

L Numb r	Hits	S arch T xt	DB	Tim stamp
1	434	438/758,765.ccls.	USPAT	2002/12/18 13:54
2	599	438/775,778.ccls.	USPAT	2002/12/18 13:55
3	207	438/791.ccls.	USPAT	2002/12/18 13:55
4	79	kato-hitoshi.in. fukushima-kohei.in. endo-atsushi.in. nishita-tatsuo.in. kumagai-takeshi.in.	USPAT	2002/12/18 13:58
5	12	kato-hitoshi.in. fukushima-kohei.in. endo-atsushi.in. nishita-tatsuo.in. kumagai-takeshi.in.	US-PGPUB	2002/12/18 13:57
6	843	kato-hitoshi.in. fukushima-kohei.in. endo-atsushi.in. nishita-tatsuo.in. kumagai-takeshi.in.	EPO; JPO; DERWENT; IBM_TDB	2002/12/18 13:57
7	28	(hexachloro\$silane \$chlorodisilane "si.sub.2cl.sub.6" "si2cl6") and (ammon\$4 "nh.sub.3" "nh3") and nitrid\$6	USPAT	2002/12/18 14:03
8	10	(hexachloro\$silane \$chlorodisilane "si.sub.2cl.sub.6" "si2cl6") and (ammon\$4 "nh.sub.3" "nh3") and nitrid\$6	EPO; JPO; DERWENT; IBM_TDB	2002/12/18 14:02
9	14	(hexachloro\$silane \$chlorodisilane "si.sub.2cl.sub.6" "si2cl6") and (ammon\$4 "nh.sub.3" "nh3") and nitrid\$6	US-PGPUB	2002/12/18 14:02
10	3575	(silicon adj2 nitride) and (react\$3 chamber vessel) and \$silane and ammon\$4	USPAT	2002/12/18 15:26
12	325	(silicon adj2 nitride) and (react\$3 chamber vessel) and \$silane and ammon\$4	EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:24
14	1949	((silicon adj2 nitride) and (react\$3 chamber vessel) and \$silane and ammon\$4) and ((silicon adj2 nitride) same (react\$3 chamber vessel))	USPAT	2002/12/18 15:27